

## CLAIMS:

1. (currently amended) A level shifting circuit comprising  
a first MOS transistor whose first terminal is connected to a first port and whose second terminal is connected to a second port,  
a second MOS transistor of the same conductivity type as the [aforementioned] first MOS transistor, whose first terminal is connected to a power supply voltage terminal that supplies a power supply voltage corresponding to a reference logic level and whose second terminal and gate terminal are both connected to the gate terminal of the [aforementioned] first MOS transistor, and  
a bias means for supplying a prescribed bias voltage below the [aforementioned] power supply voltage to the gate terminal of the aforementioned first MOS transistor.

2. (currently amended) The level shifting circuit of Claim 1, comprising a first clamping circuit connected between the [aforementioned] power supply voltage terminal and the [aforementioned] first port in order to clamp the potential at the [aforementioned] first port close to the [aforementioned] reference logic level.

3. (currently amended) The level shifting circuit of Claim 1, comprising a first switch wherein the [aforementioned] first clamping circuit is turned off when the potential levels of the [aforementioned] first and second ports have logic levels different from the [aforementioned] reference logic level, and it is turned on when the potential of one of the [aforementioned] first [and/or] and the second port has a logic level equal to the [aforementioned] reference logic level.

4. (currently amended) The level shifting circuit of Claim 2 [or 3], wherein the [aforementioned] first clamping circuit is provided with a first diode for allowing a current to flow in the forward direction from the [aforementioned] power supply voltage terminal to the [aforementioned] first port.

5. (currently amended) The level shifting circuit of [one of Claims 2-4] Claim 2, wherein the [aforementioned] first clamping circuit is provided with a first constant current source circuit for allowing a constant current to flow from the [aforementioned] power supply voltage terminal to the [aforementioned] first port.

6. (currently amended) The level shifting circuit of [one of Claims 1-5] Claim 1 comprising a second clamping circuit connected between the [aforementioned] power supply voltage terminal and the [aforementioned] second port in order to clamp the potential of the [aforementioned] second port near the [aforementioned] reference logic level.

7. (currently amended) The level shifting circuit of Claim 6, further comprising a second switch wherein the [aforementioned] second clamping circuit is turned off when the potential levels of the [aforementioned] first and the second ports have logic levels different from the [aforementioned] reference logic level, and it is turned on when the potential of one of the [aforementioned] first [and/or] and the second [port] ports is logically equal to the aforementioned reference logic level.

8. (currently amended) The level shifting circuit of Claim 6 [or 7], wherein the [aforementioned] second clamping circuit is provided with a second diode for allowing a current to flow in the forward direction from the [aforementioned] power supply voltage terminal to the [aforementioned] second port.

9. (currently amended) The level shifting circuit of described under [one of Claims 6-8] Claim 6, wherein the [aforementioned] second clamping circuit is provided with a second constant current source circuit for allowing a constant current to flow from the [aforementioned] power supply voltage terminal to the [aforementioned] second port.

10. (currently amended) The level shifting circuit of [one of Claims 1-9] Claim 1, further comprising a third diode whose anode is connected to the [aforementioned] first port, and whose cathode is connected to the gate terminal of the [aforementioned] first MOS transistor.

11. (currently amended) The level shifting circuit of Claim 10, further comprising a first resistor connected in series with the [aforementioned] third diode between the [aforementioned] first port and the gate terminal of the [aforementioned] first MOS transistor.

12. (currently amended) The level shifting circuit of Claim 10, further comprising a third constant current source circuit connected in series with the [aforementioned] third diode between the [aforementioned] first port and the gate terminal of the [aforementioned] first MOS transistor.

13. (currently amended) The level shifting circuit of [one of Claims 1-12] Claim 1, further comprising a fourth diode whose anode is connected to the [aforementioned] second port, and whose cathode is connected to the gate terminal of the [aforementioned] first MOS transistor.

14. (currently amended) The level shifting circuit of Claim 13, further comprising a second resistor connected in series with the [aforementioned] fourth diode between the [aforementioned] second port and the gate terminal of the [aforementioned] first MOS transistor.

15. (currently amended) The level shifting circuit of Claim 13, further comprising a fourth constant current source circuit connected in series with the [aforementioned] fourth diode between the [aforementioned] second port and the gate terminal of the [aforementioned] first MOS transistor.

16. (currently amended) The level shifting circuit of [one of Claims 1-15] Claim 1, wherein the [aforementioned] bias means is provided with a fifth diode whose anode is connected to the [aforementioned] power supply voltage terminal, and whose cathode is connected to the gate terminal of the [aforementioned] first MOS transistor.

17. (currently amended) The level shifting circuit of Claim 16, further comprising

a third switch connected in series with the [aforementioned] fifth diode the [aforementioned] power supply voltage terminal and the gate terminal of the [aforementioned] first MOS transistor,

a fourth switch connected between the gate terminal of the [aforementioned] first MOS transistor and a reference potential logic level different from the [aforementioned] reference logic level, and

a switch control means that turns the [aforementioned] third switch on and the [aforementioned] fourth switch off and vice versa.

18. (currently amended) The level shifting circuit of Claim 17, further comprising a voltage amplifier which increases the potential of the gate terminal of the [aforementioned] first MOS transistor to a level higher than the [aforementioned] power supply voltage in response to a control signal given by the [aforementioned] switch control means in order to turn the [aforementioned] third switch on and turn the [aforementioned] fourth switch off.

19. (currently amended) The level shifting circuit of Claim 18, wherein the [aforementioned] voltage amplifier circuit is provided with a delayed voltage output circuit that increases its output voltage from a logic level different from the [aforementioned] reference logic level to a logic level equal to the [aforementioned] reference logic level after a prescribed delay time has passed after the [aforementioned] control signal is input, as well as with a capacitor connected between the output terminal of the [aforementioned] delayed voltage output circuit and the gate terminal of the [aforementioned] first MOS transistor.

20. (currently amended) The level shifting circuit of [one of Claims 1-17] Claim 1, further comprising a third MOS transistor whose first terminal is connected to the [aforementioned] first port and whose second terminal is connected to the [aforementioned] second port,

a fourth MOS transistor of the same conductivity type as the [aforementioned] third MOS transistor whose first terminal is connected to the [aforementioned] power supply

voltage terminal and whose second terminal and gate terminal are both connected to the gate terminal of the [aforementioned] third MOS transistor,

a sixth diode whose anode is connected to the [aforementioned] power supply voltage terminal and whose cathode is connected to the gate terminal of the [aforementioned] third MOS transistor,

a fifth switch connected in series with the [aforementioned] sixth diode between the [aforementioned] power supply voltage terminal and the gate terminal of the [aforementioned] third MOS transistor,

a sixth switch connected between the gate terminal of the [aforementioned] third MOS transistor and a reference potential having a logic level different from the [aforementioned] reference logic level,

a switch control means that turns the [aforementioned] fifth switch on and the [aforementioned] sixth switch off and vice versa, and

a voltage amplifier that increases the potential of the gate terminal of the [aforementioned] third MOS transistor to a level higher than the [aforementioned] power supply voltage in response to a control signal given by the [aforementioned] switch control means in order to turn the [aforementioned] fifth switch on and turn the [aforementioned] sixth switch off.

21. (currently amended) The level shifting circuit of Claim 20, wherein the [aforementioned] voltage amplifier is provided with a delayed voltage output circuit that increases its output voltage from a logic level different from the [aforementioned] reference logic level to a logic level equal to the [aforementioned] reference logic level after a prescribed amount of delay time has passed after the [aforementioned] control signal is input, as well as with a capacitor connected between the output terminal of the [aforementioned] delayed voltage output circuit and the gate terminal of the [aforementioned] third MOS transistor.

22. (currently amended) A level shifting circuit comprising a first MOS transistor connected between a first input/output terminal and a second input/output terminal,

a second MOS transistor connected between a first power supply voltage terminal and the gate terminal of the [aforementioned] first MOS transistor and whose gate terminal is connected to the gate terminal of the [aforementioned] first MOS transistor,

a first rectifying element connected between a first power supply voltage terminal and the gate terminal of the [aforementioned] first MOS transistor in order to source current from the first power supply voltage terminal to the gate terminal of the [aforementioned] first MOS transistor,

a second rectifying element connected between the [aforementioned] first input/output terminal and the gate terminal of the [aforementioned] first MOS transistor in order to source current from the [aforementioned] first input/output terminal to the gate terminal of the [aforementioned] first MOS transistor,

a third rectifying element connected between the [aforementioned] second input/output terminal and the gate terminal of the [aforementioned] first MOS transistor in order to source current from the [aforementioned] second input/output terminal to the gate terminal of the [aforementioned] first MOS transistor,

a third MOS transistor connected between the first power supply voltage terminal and the [aforementioned] first input/output terminal,

a fourth rectifying element connected between the [aforementioned] third MOS transistor and the [aforementioned] first input/output terminal in order to source current from the first power supply voltage terminal to the [aforementioned] first input/output terminal,

a fourth MOS transistor connected between the first power supply voltage terminal and the [aforementioned] second input/output terminal,

a fifth rectifying element connected between the [aforementioned] fourth MOS transistor and the [aforementioned] second input/output terminal in order to source current from the first power supply voltage terminal to the [aforementioned] second input/output terminal, and

a logic circuit whose first and second input terminals are connected to the [aforementioned] first and the second input/output terminals, respectively, in order to output a control signal to turn on the [aforementioned] fourth and fifth MOS transistors when the voltage level of the [aforementioned] first and/or the second input/output terminal corresponds to the [aforementioned] power supply voltage.

23. (currently amended) The level shifting circuit of Claim 22, wherein the [aforementioned] first and second MOS transistors are NMOS transistors, the [aforementioned] third and fourth MOS transistors are PMOS transistors, the [aforementioned] first rectifying element is a diode whose anode is connected to the first power supply voltage terminal and whose cathode is connected to the gate terminal of the [aforementioned] first MOS transistor, the [aforementioned] second rectifying element is a diode whose anode is connected to the [aforementioned] first input/output terminal and whose cathode is connected to the gate terminal of the [aforementioned] first MOS transistor, the [aforementioned] third rectifying element is a diode whose anode is connected to the [aforementioned] second input/output terminal and whose cathode is connected to the gate terminal of the [aforementioned] first MOS transistor, the [aforementioned] fourth rectifying element is a diode whose anode is connected to the [aforementioned] third MOS transistor and whose cathode is connected to the [aforementioned] first input/output terminal, and the [aforementioned] fifth rectifying element is a diode whose anode is connected to the [aforementioned] fourth MOS transistor and whose cathode is connected to the [aforementioned] second input/output terminal.

24. (currently amended) The level shifting circuit of Claim 22 [or 23], comprising a fifth MOS transistor connected between the [aforementioned] first rectifying element and the gate terminal of the [aforementioned] first MOS transistor in order to cut off the current path formed between the [aforementioned] first rectifying element and the gate terminal of the [aforementioned] first MOS transistor, the current path between the [aforementioned] second rectifying element and the gate terminal of the [aforementioned] first MOS transistor, and the current path between the [aforementioned] third rectifying element and the gate terminal of the [aforementioned] first MOS transistor, a sixth MOS transistor connected between the gate terminal of the [aforementioned] first MOS transistor and the [aforementioned] second power supply voltage terminal, and

a control circuit that supplies a control signal in order to make the [aforementioned] fifth MOS transistor and the [aforementioned] sixth MOS transistor conductive in a complementary manner.

Respectfully submitted,  
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A handwritten signature in black ink, appearing to read 'W. B. Kempfer', with a stylized flourish at the end.

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